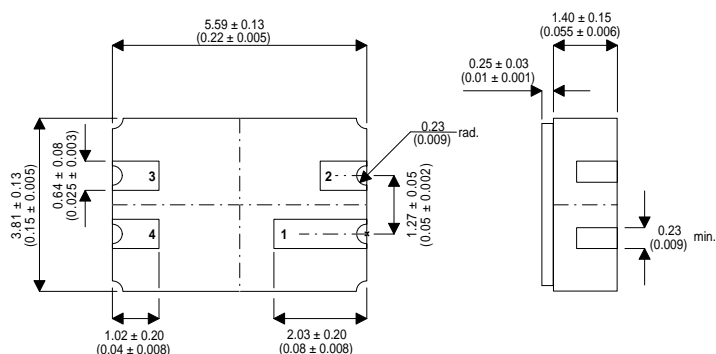


MECHANICAL DATA

Dimensions in mm (inches)



(LCC3 PACKAGE)
Underside View

PAD 1 — Cathode PAD 3 — No Connection
PAD 2 — No Connection PAD 4 — Anode

GENERAL PURPOSE SILICON RECTIFIER DIODE

General Purpose Rectifier Diode
In Hermetic Ceramic Surface Mount Package
For High Reliability Applications

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_R	Reverse Voltage			200	V
V_{RRM}	Peak Reverse Voltage			200	V
$I_{F(AV)}$	Average Half Wave Rectified Forward Current	$T_{amb} \leq 25^{\circ}\text{C}$		1.0	A
		$T_{amb} = 100^{\circ}\text{C}$		0.75	
I_F	D.C Forward Current			1	A
I_{FRM}	Repetitive Peak Forward Current			10	A
I_{FSM}	Non-Repetitive Peak Forward Current	(half cycle surge , 60 c.p.s)		30	A

T_{stg}	Storage Temperature Range	-55 to +175 °C
T_j	Max junction temperature	+150°C

CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Forward Voltage Drop			1.1	V
$V_{F(AV)}$	Full-Cycle average forward voltage drop			0.8	V
I_R	Reverse Current	$V_R = 50\text{ V} , T_{amb} = 25^{\circ}\text{C}$		10	μA
		$V_R = 50\text{ V} , T_{amb} = 100^{\circ}\text{C}$		50	
$I_{R(AV)}$	Full cycle average reverse current	$V_{RRM} = 50\text{ V} , T_{amb} = 75^{\circ}\text{C}$		30	μA